### **Experiment No.: 5**

# JFET Amplifier

ADITYA RAJ U20CS100

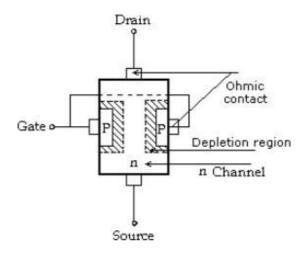
**AIM:** To study output and transfer characteristics of an n-channel Junction field effect Transistor (JFET) Amplifier

#### **SOFTWARE TOOLS / OTHER REQUIREMENTS:**

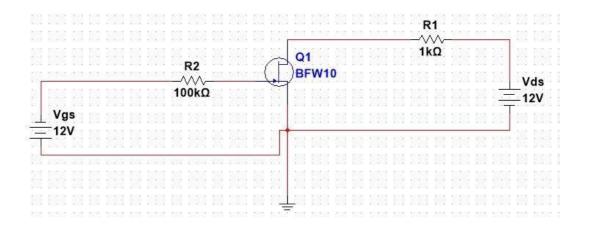
Multisim Simulator/Circuit Simulator

#### **THEORY:**

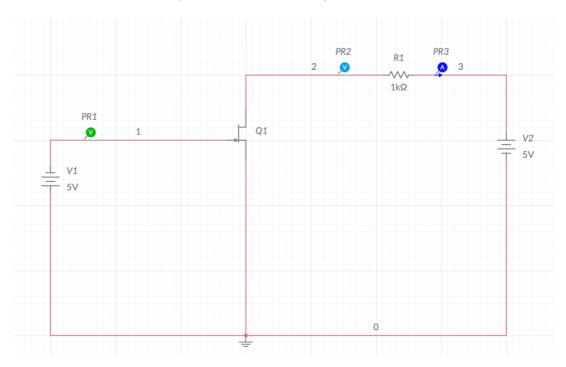
The basic construction of n-channel JFET is as shown in figure. The major part of JFET is the channel between embedded P types of material. The top of the n-channel is connected to an ohmic contact called as 'Drain' (D) & lower end of Channel is called as 'Source' (S). The two p types of materials are connected together & to the 'Gate' terminal (G).



**CIRCUIT DIAGRAM:** 



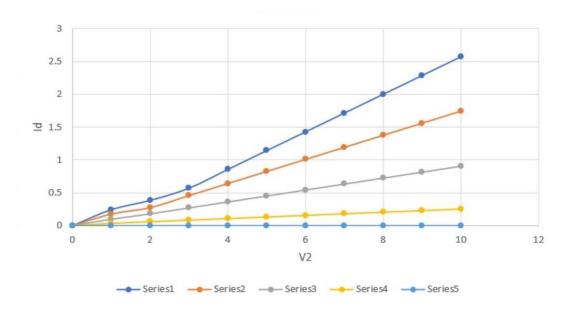
#### **CIRCUIT DIAGRAM (FROM MULTISIM)**



#### **OUTPUT CHARACTERISTICS**

	$V_1 = 0V$	V <sub>1</sub> = -0.5V	V <sub>1</sub> = -1V	V <sub>1</sub> = -1.5V	V <sub>1</sub> = -2V
$V_2(V)$	$I_d$ (mA)	$I_d(mA)$	$I_d(mA)$	$I_d(mA)$	$I_d$ (mA)
0	0	0	0	0	0

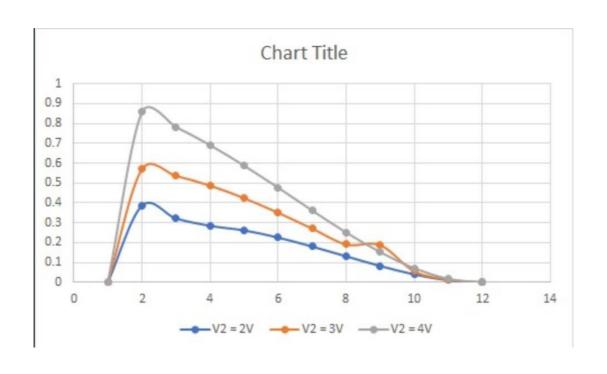
1	0.245	0.178	0.099	0.036	0
2	0.385	0.275	0.181	0.061	0
3	0.571	0.459	0.272	0.085	0
4	0.857	0.642	0.363	0.109	0
5	1.143	0.826	0.454	0.134	0
6	1.428	1.010	0.545	0.158	0
7	1.714	1.193	0.636	0.183	0
8	2	1.377	0.727	0.207	0
9	2.285	1.561	0.818	0.231	0
10	2.571	1.745	0.909	0.256	0



## INPUT CHARACTERISTICS

	$V_2 = 2V$	$V_2 = 3V$	$V_2 = 4V$
$V_1(V)$	$I_d(mA)$	$I_d(mA)$	$I_d(mA)$

0	0.385	0.571	0.857
-0.2	0.322	0.538	0.783
-0.4	0.285	0.489	0.692
-0.6	0.262	0.426	0.589
-0.8	0.226	0.352	0.478
-1.0	0.181	0.272	0.363
-1.2	0.132	0.192	0.252
-1.4	0.083	0.188	0.153
-1.6	0.041	0.056	0.072
-1.8	0.011	0.015	0.019
-2.0	0	0	0



## **Conclusions:**

JFET IS A FIELD EFFECT TRANSISTOR WHICH IS A VOLTAGE CONTROLLED CURRENT SOURCE HAVING EXTREMELY HIGH INPUT IMPEDANCE. UNLIKE BJT, IT IS A UNIPOLAR JUNCTION TRANSISTOR WHICH IS USED IN MANY ELECTRONIC DEVICES AS AN AMPLIFIER.